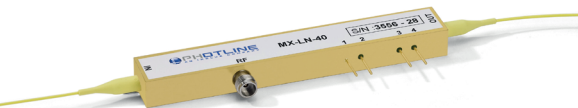


MX-LN series

1550 nm band Intensity Modulators

PHOTLINE MODULATOR



FEATURES

- High bandwidth
- X-cut for high stability
- Low drive voltage
- Low insertion loss

APPLICATIONS

- Digital communications
- General purpose intensity modulation
- Test and measurement

OPTIONS

- High extinction ratio versions
- 2000 nm, 1300 nm, 1060 nm, 850 nm

RELATED EQUIPMENTS

- RF amplifiers
- MBC-DG Automatic Bias Controllers
- ModBox-1550nm-44Gb/s-NRZ

The Photline MX-LN series are lithium niobate (LiNbO_3) intensity modulators designed for optical communications at data rates up to 44 Gb/s.

The X-cut design of these Mach-Zehnder modulators confer them an unmatched stability in a wide range of operational conditions, as well as a zero chirp performance. Ixblue proprietary waveguide design offers a low insertion loss combined with a high contrast. The MX-LN series are ideally suited for 10 Gb/s up to 44 Gb/s optical transmission with NRZ, RZ, DPSK, Duo Binary modulation formats and are key device for a large variety of high bandwidth applications.

MX-LN-10 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss (option low IL)	-	2.7	-	dB
Electro-optical bandwidth	-	12	-	GHz
V_{π} RF @50 kHz	-	4	-	V

Specifications given at 25 °C, 1550 nm

MX-LN-20 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss (option low IL)	-	2.7	-	dB
Electro-optical bandwidth	-	25	-	GHz
V_{π} RF @50 kHz	-	5	-	V

Specifications given at 25 °C, 1550 nm

MX-LN-40 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss	-	4	-	dB
Electro-optical bandwidth	-	30	-	GHz
V_{π} RF @50 kHz	-	5	-	V

Specifications given at 25 °C, 1550 nm

MX-LN-10

10 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	10	12	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 12$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
V_{π} RF @50 kHz	$V_{\pi RF_{50\text{ kHz}}}$	RF electrodes, @1550 nm	-	4	5	V
V_{π} RF @10 Gb/s PRBS	$V_{\pi RF_{10\text{ Gb/s}}}$	RF electrodes, @1550 nm	-	4.7	5.7	V
V_{π} DC electrodes	$V_{\pi DC}$	DC electrodes	-	4	5	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	-	1	-	M Ω

A DC block may be required at the RF input to isolate driving electronics from the DC bias voltage
 50 Ω RF input

Optical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	4.5	dB
		Option Low IL, without connectors	-	2.7	3	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

All specifications given at 25°C, 1550 nm, unless differently specified

Absolute Maximum Ratings

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	26	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

MX-LN-20

20 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	20	25	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 20$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
$V\pi$ RF @50 kHz	$V\pi_{RF, 50\text{ kHz}}$	RF electrodes, @1550 nm	-	5	5.5	V
$V\pi$ RF @20 Gb/s PRBS	$V\pi_{RF, 20\text{ Gb/s}}$	RF electrodes, @1550 nm	-	5.5	6	V
$V\pi$ DC electrodes	$V\pi_{DC}$	DC electrodes	-	6.5	7	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	-	1	-	M Ω

 50 Ω RF input

Optical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	4.5	dB
		Option Low IL, without connectors	-	2.7	3	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

All specifications given at 25 °C, 1550 nm, unless different specified

Absolute Maximum Ratings

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Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	28	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

MX-LN-40

40 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	28	30	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 30$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
V_{π} RF @50 kHz	$V_{\pi RF_{50\text{ kHz}}}$	RF electrodes, @1550 nm	-	5	6	V
V_{π} DC electrodes	$V_{\pi DC}$	DC electrodes, @1550 nm	-	6.5	7	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	1	-	-	M Ω

50 Ω RF input

Optical Characteristics

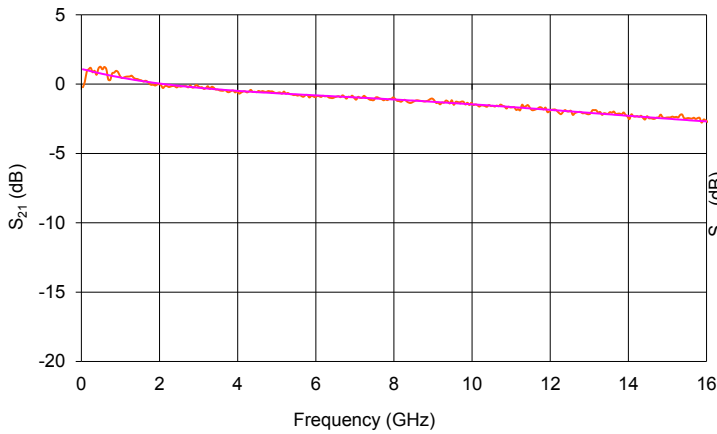
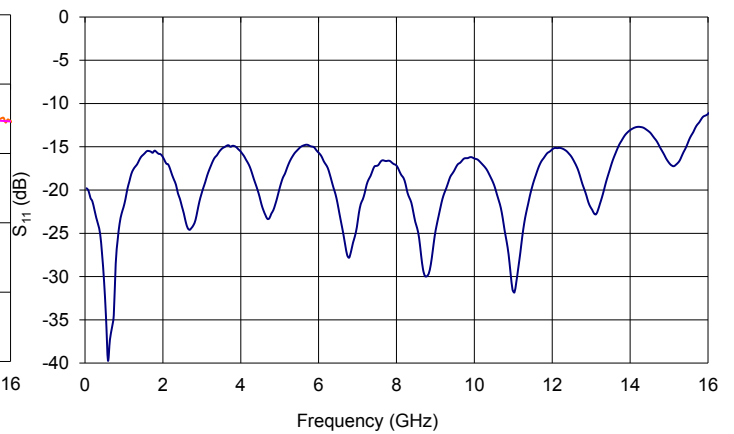
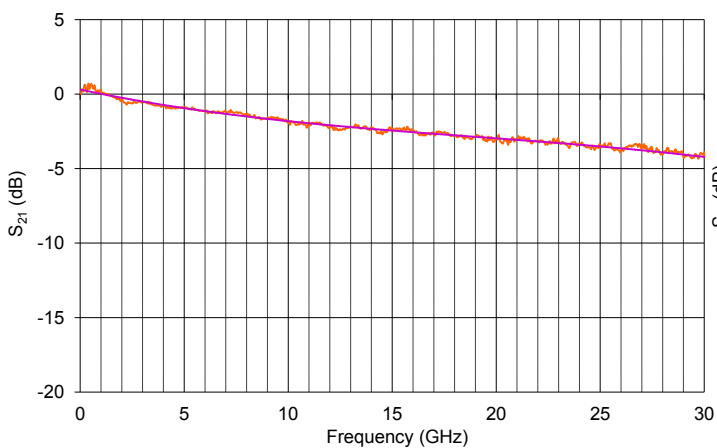
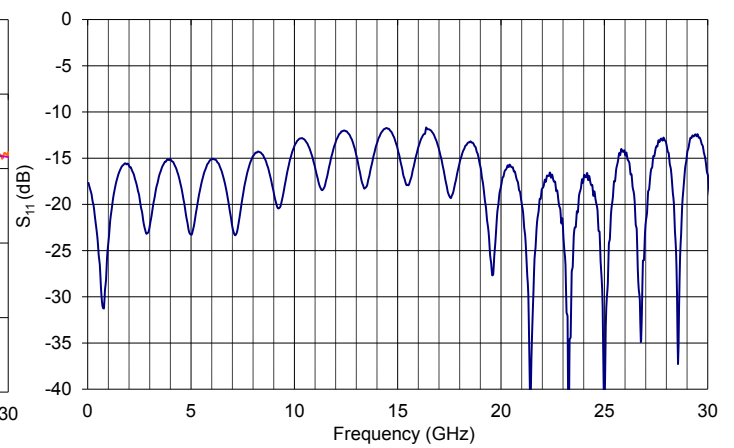
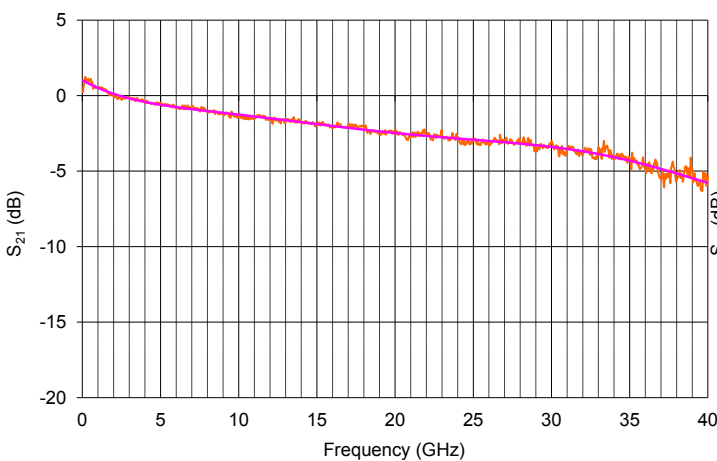
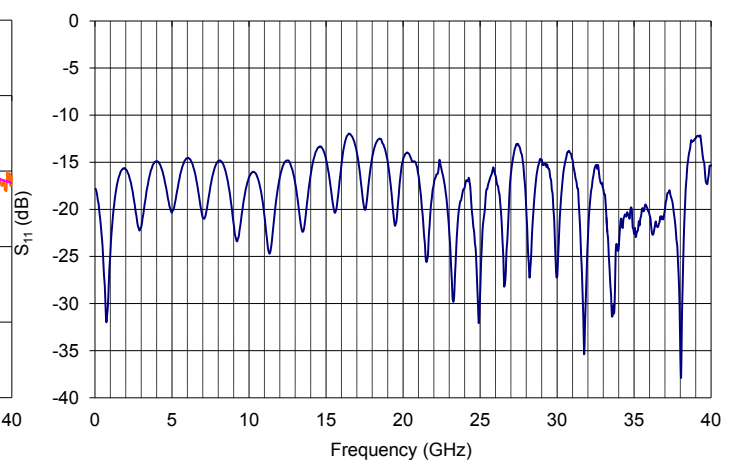
Parameter	Symbol	Condition	Min	Typ	Max	Unit
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Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	4.5	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

All specifications given at 25 °C, 1550 nm, unless different specified

Absolute Maximum Ratings

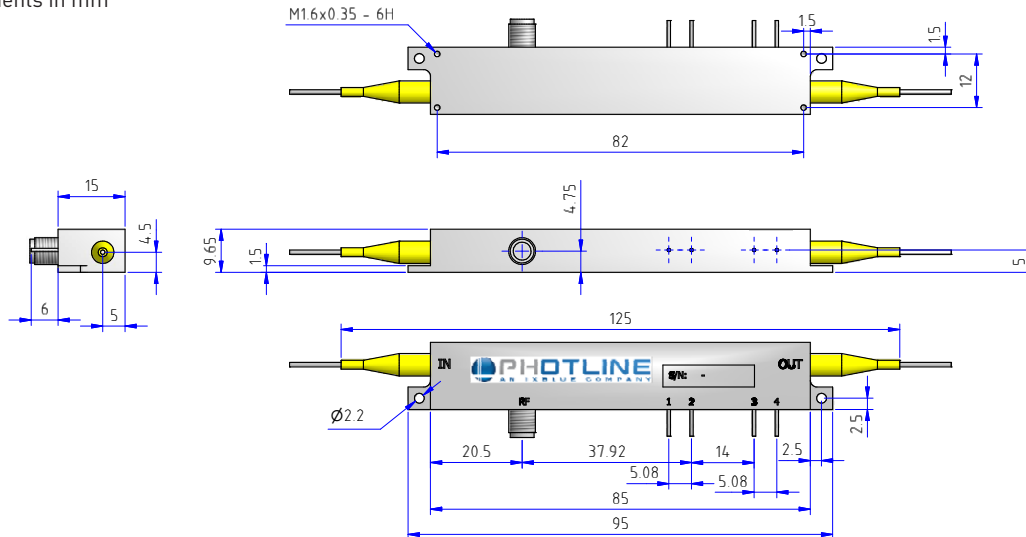
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Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	28	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

MX-LN-10 Typical S_{21} Curve

MX-LN-10 Typical S_{11} Curve

MX-LN-20 Typical S_{21} Curve

MX-LN-20 Typical S_{11} Curve

MX-LN-40 Typical S_{21} Curve

MX-LN-40 Typical S_{11} Curve


Mechanical Diagram and Pinout

All measurements in mm



Port	Function	Note
IN	Optical input port	Polarization maintaining fiber, Corning PM 15-U25D, Length 1.5 meter. Buffer diameter 900 μ m
OUT	Optical output port	Polarization maintaining fiber, Corning PM 15-U25D, Length 1.5 meter. Buffer diameter 900 μ m
RF	RF input port	MX-LN-10: Wiltron female K (SMA compatible) MX-LN-20: Wiltron female K or V (optional) MX-LN-40: Wiltron female V
1	Ground	Pin feed through diameter 1.0 mm
2	DC	Pin feed through diameter 1.0 mm
3, 4	Photodiode cathode, anode	Pin feed through diameter 1.0 mm

Ordering information

MX-LN-BW-XX-Y-Z-AB-CD

BW = Bandwidth : 10 10 GHz 20 20 GHz 40 40 GHz

XX = Internal photodiode : 00 Not integrated PD PD Integrated

Y = Input fiber : P Polarization maintaining S Standard single mode

Z = Output fiber : P Polarization maintaining S Standard single mode

AB = Input connector : 00 bare fiber FA FC/APC FC FC/SPC

CD = Output connector : 00 bare fiber FA FC/APC FC FC/SPC

Note : optical connectors are Seikoh-Giken with narrow key or equivalent

About us

iXBlue Photonics includes iXBlue iXFiber brand that produces specialty optical fibers and Bragg gratings based fiber optics components and iXBlue Photline brand that provides optical modulation solutions based on the company lithium niobate (LiNbO_3) modulators and RF electronic modules.

iXBlue Photonics serves a wide range of industries : sensing and instruments, defense, telecommunications, space and fiber lasers as well as research laboratories all over the world.

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